N-Channel Super Junction Power MOSFET Ⅳ

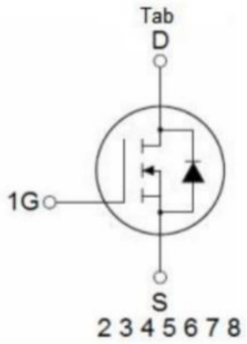
General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

$V_{DS\ min@Tjmax}$	710	V
$R_{DS(ON)TYP}$	60	mΩ
ID	45	A
Qg	65	nC

Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant



Schematic diagram

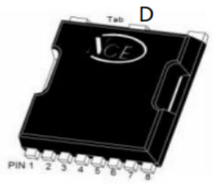
✧ **Intrinsic fast-recovery body diode**

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）
- LLC Half-bridge

Package Marking And Ordering Information

Device	Device Package	Marking
NCE65NF068LL	TOLL-8L	NCE65NF068LL



TOLL-8L

Pin1:G

Pin2:k-source

Pin3~8:source

Table 1. Absolute Maximum Ratings (T_J=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (VGS=0V）	V_{DS}	650	V
Gate-Source Voltage (VDS=0V) AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (VDS=0V) DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	45	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	31.5	A
Pulsed drain current (Note 1)	$I_{DM\ (pluse)}$	135	A
Maximum Power Dissipation(Tc=25°C) Derate above 25°C	P_D	371 2.47	W W/°C
Single pulse avalanche energy (Note 2)	E_{AS}	400	mJ
Avalanche current(Note 1)	I_{AS}	10	A
Repetitive Avalanche energy ， t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.9	mJ
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.40	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (T_J=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=1mA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			300	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=500μA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=23A		60	68	mΩ
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		3900	4400	pF
Output Capacitance	C_{oss}			132		pF
Reverse Transfer Capacitance	C_{rss}			14		pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=23A, V_{GS}=10V		65		nC
Gate-Source Charge	Q_{gs}			21		nC
Gate-Drain Charge	Q_{gd}			17		nC
Gate plateau voltage	Vgp			6.5		V
Intrinsic gate resistance	R_G	f = 1 MHz open drain		3		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=23A, R_G=1.7Ω,V_{GS}=10V		42		nS
Turn-on Rise Time	t_r			14		nS
Turn-Off Delay Time	$t_{d(off)}$			90		nS
Turn-Off Fall Time	t_f			12		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			45	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				135	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=45A,V_{GS}=0V		1.0	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=23A, di/dt=100A/μs		173		nS
Reverse Recovery Charge	Q_{rr}			1.13		uC
Peak Reverse Recovery Current	I_{rrm}			13		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

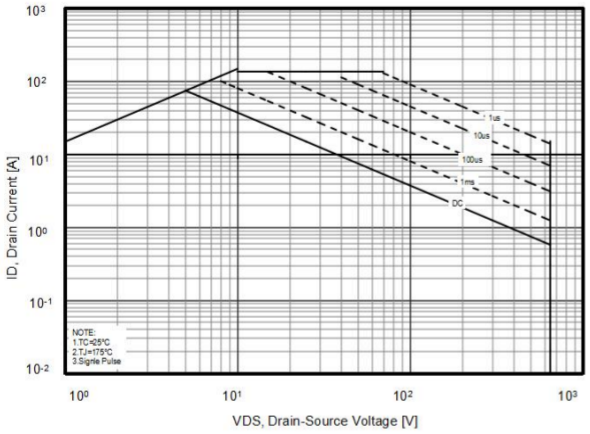


Figure2. Capacitance

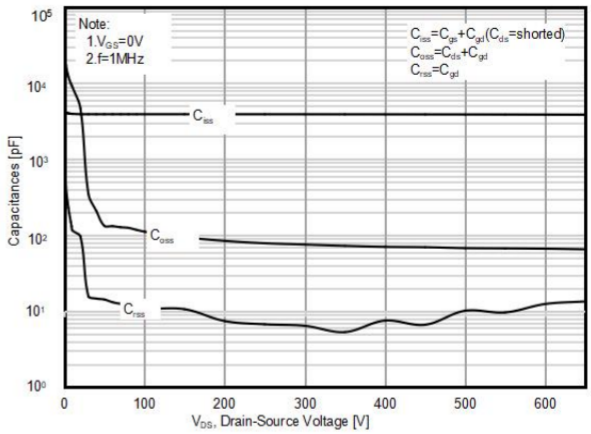


Figure3. Source-Drain Diode Forward Voltage

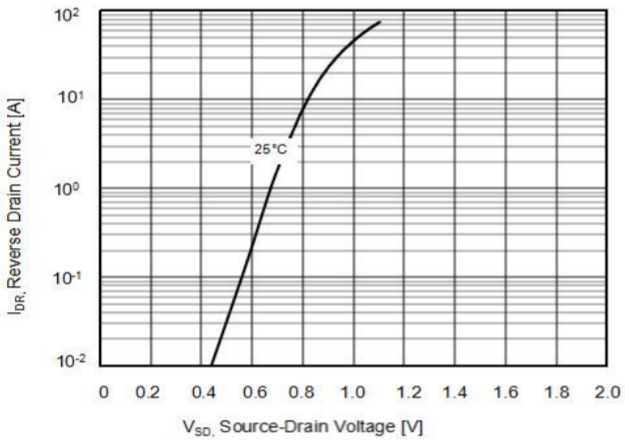


Figure4. Output characteristics

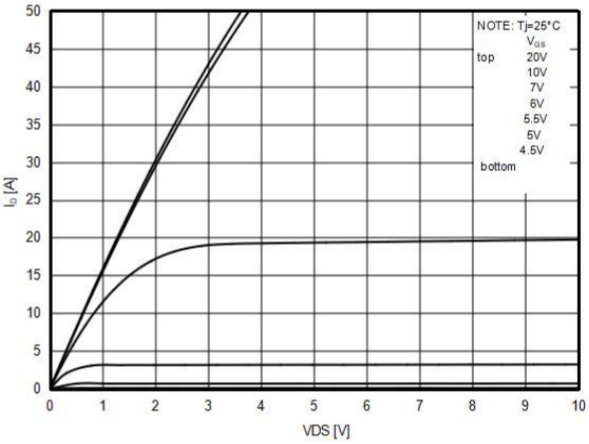


Figure5. $R_{DS(ON)}$ vs Junction Temperature

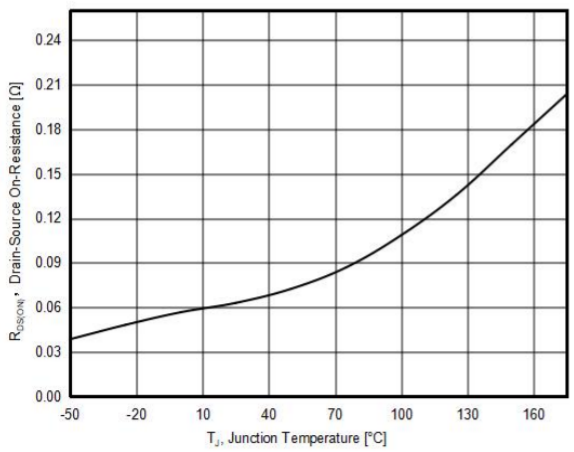


Figure6. BV_{DSS} vs Junction Temperature

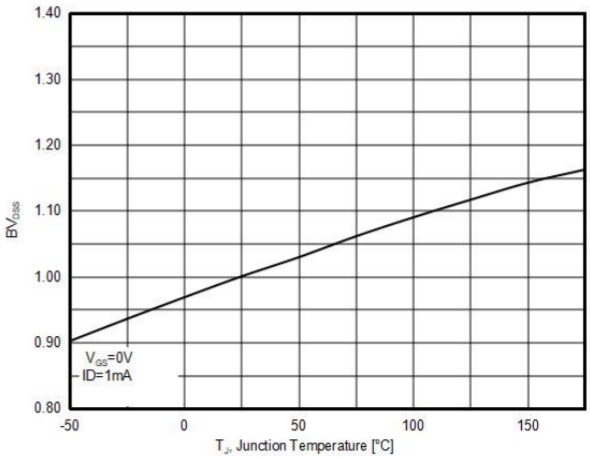


Figure7. Maximum I_D vs Junction Temperature

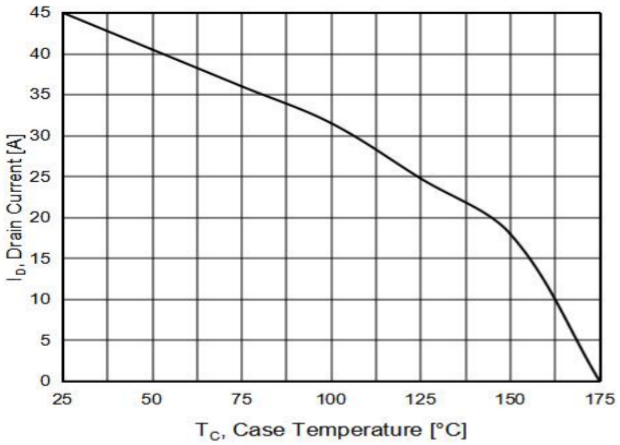


Figure8. Gate charge waveforms

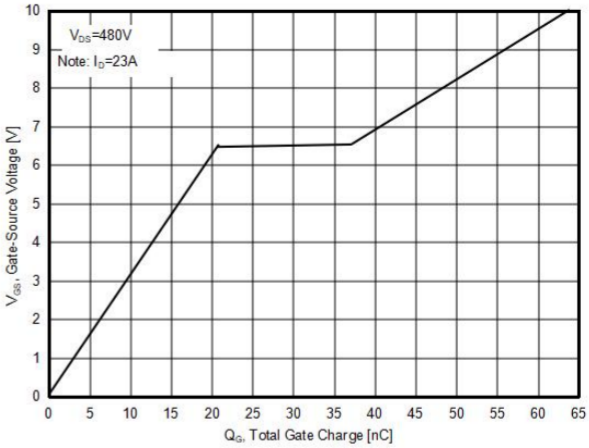


Figure9. Static drain-source on resistance

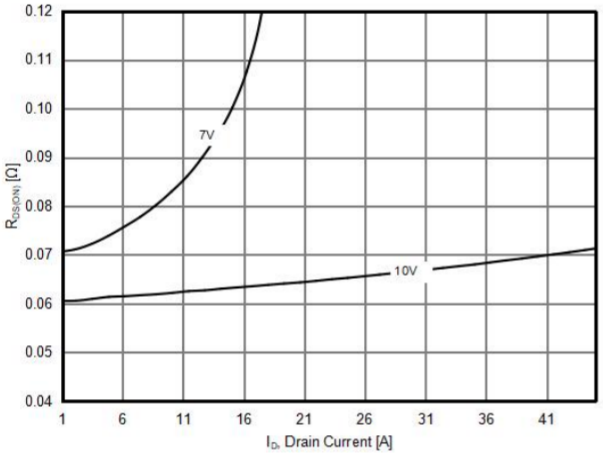
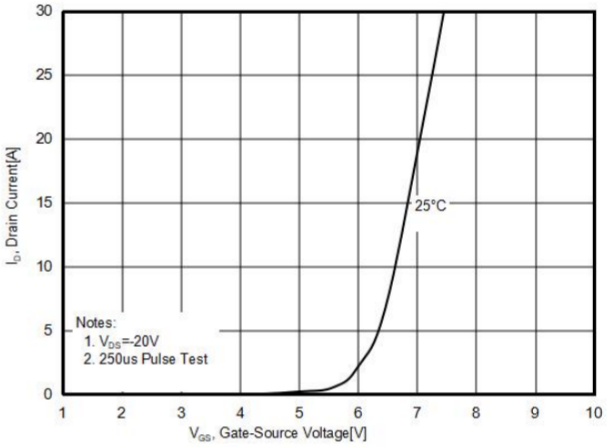
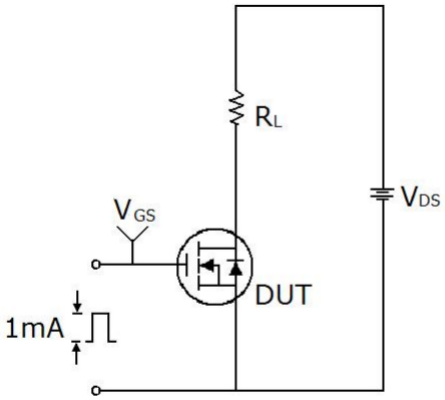


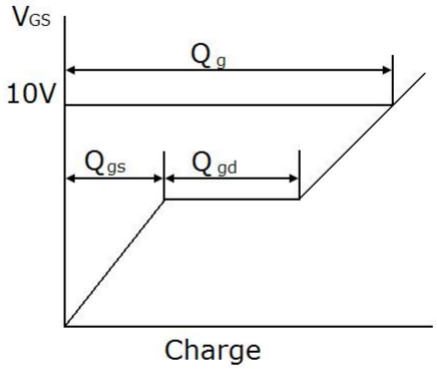
Figure10. Transfer characteristics



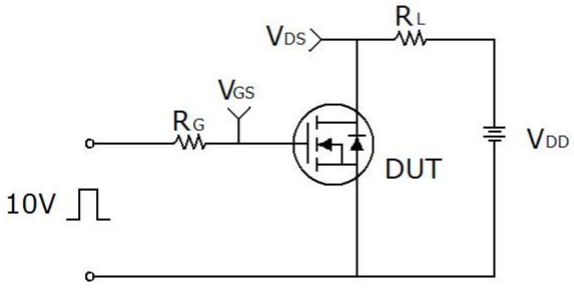
Test circuit

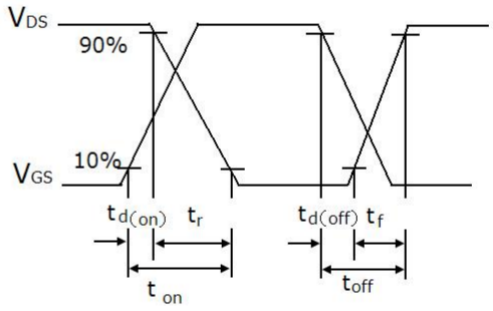
1）Gate charge test circuit & Waveform



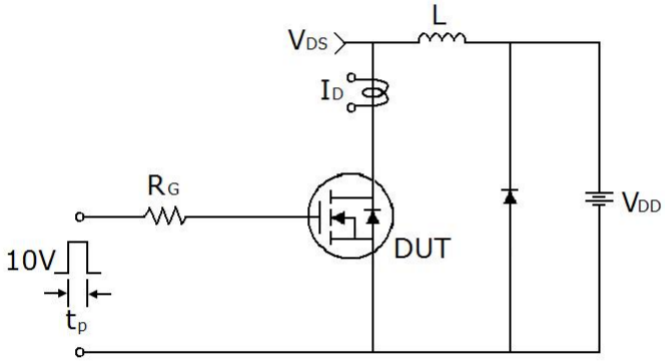


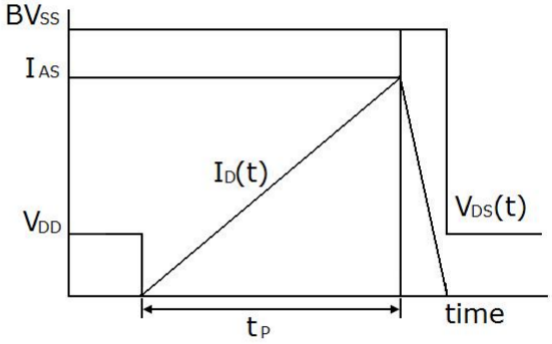
2）Switch Time Test Circuit：



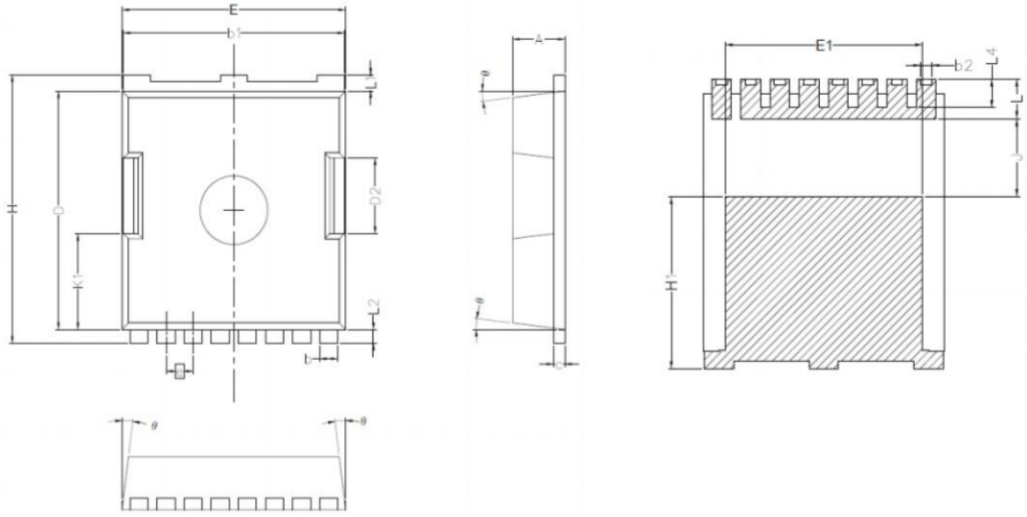


3）Unclamped Inductive Switching Test Circuit & Waveforms





TOLL-8L-B Package Information



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min.	Typ	Max.	Min.	Typ	Max.
A	2.20		2.40	0.09		0.09
b	0.70		0.90	0.03		0.04
b1	9.70		9.90	0.38		0.39
b2	0.42		0.50	0.02		0.02
c	0.40		0.60	0.02		0.02
D	10.28		10.58	0.40		0.42
D2	3.10	3.30	3.50	0.12		0.14
E	9.70	9.90	10.10	0.38		0.40
E1	7.90	8.10	8.30	0.31		0.33
e	1.20 BSC			0.05 BSC		
H	11.48	11.68	11.88	0.45	0.46	0.47
H1	6.75	6.95	7.15	0.27	0.27	0.28
N	8.00			0.31		
J	3.00	3.15	3.30	0.12	0.12	0.13
K1	3.98	4.18	4.38	0.16	0.16	0.17
L	1.40	1.60	1.80	0.06	0.06	0.07
L1	0.60	0.70	0.80	0.02	0.03	0.03
L2	0.50	0.60	0.70	0.02	0.02	0.03
L4	1.00	1.15	1.30	0.04	0.05	0.05

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